

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((rpn) with (poly polysilicon gate electrode)) and @pd>="07082004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 15:39
S12	11	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((rpn) with (poly polysilicon gate electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 15:36
S49	48	surface near density with silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 14:01
S48	2	density with silicon near nitride with ("10.sup.22" "10.sup.23")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 14:01
S47	3573	density with silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 13:59
S45	2	denisty with silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 13:59
S46	0	denisty with ("si.sub.3 n.sub.4" "si.sub.3n.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 13:58